MBR540MFS, NRVB540MFS

Switch-mode Power Rectifiers

These state−of−the−art devices have the following features:

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free and Halide−Free Devices

Mechanical Characteristics:

- Case: Epoxy, Molded
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting SurfaceTemperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

MAXIMUM RATINGS

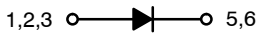
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
Average Rectified Forward Current (Rated V_R, T_C = 165°C)	$I_{F(AV)}$	5	A
Peak Repetitive Forward Current, (Rated V_R, Square Wave, 20 kHz, T_C = 165°C)	I_{FRM}	10	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Storage Temperature Range	T_{stg}	−65 to +175	°C
Operating Junction Temperature	T_J	−40 to +175	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non−repetitive)	E_{AS}	40	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

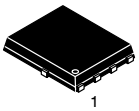
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ON Semiconductor®

http://onsemi.com

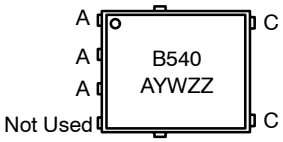
SCHOTTKY BARRIER RECTIFIERS 5 AMPERES 40 VOLTS





SO−8 FLAT LEAD CASE 488AA STYLE 2

MARKING DIAGRAM



B540 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR540MFST1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel
MBR540MFST3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel
NRVB540MFST1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel
NRVB540MFST3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction−to−Case, Steady State (Assumes 600 mm^2 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	−	4.0	°C/W

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) (i_F = 5 Amps, T_J = 100°C) (i_F = 5 Amps, T_J = 25°C)	v_F	 0.44 0.50	 0.54 0.58	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T_J = 100°C) (Rated dc Voltage, T_J = 25°C)	i_R	 6 0.100	 20 2	mA

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

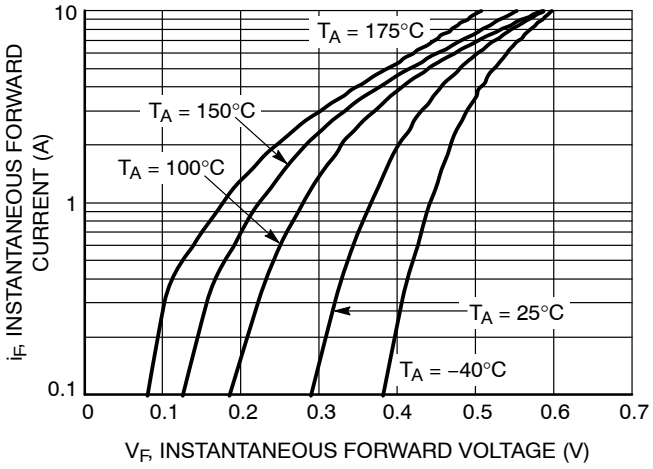


Figure 1. Typical Instantaneous Forward Characteristics

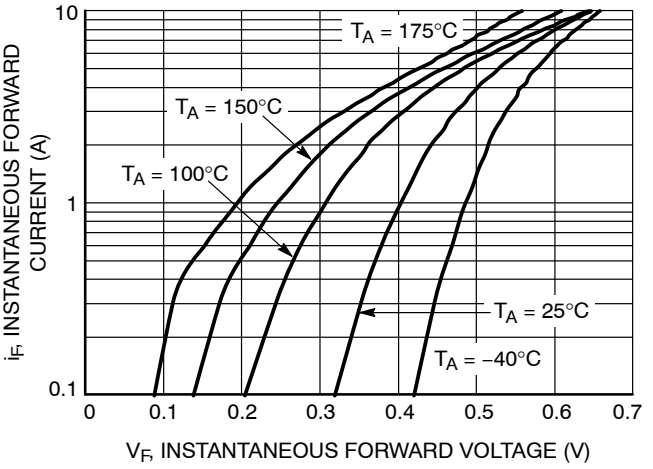


Figure 2. Maximum Instantaneous Forward Characteristics

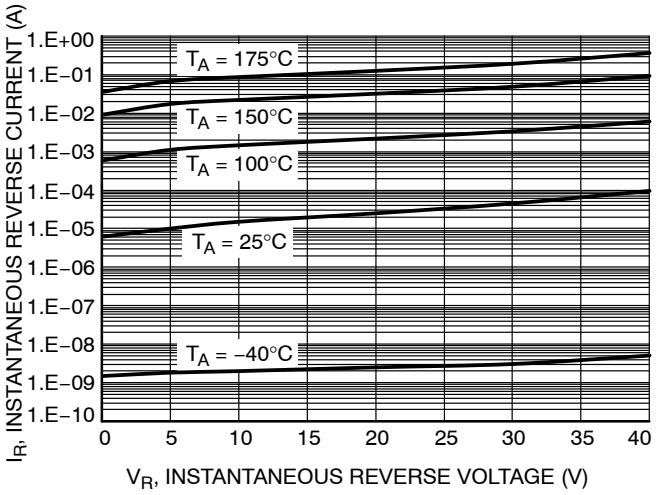


Figure 3. Typical Reverse Characteristics

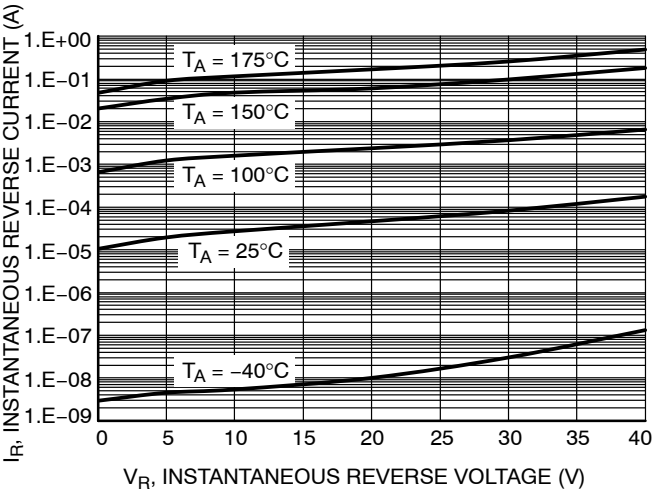


Figure 4. Maximum Reverse Characteristics

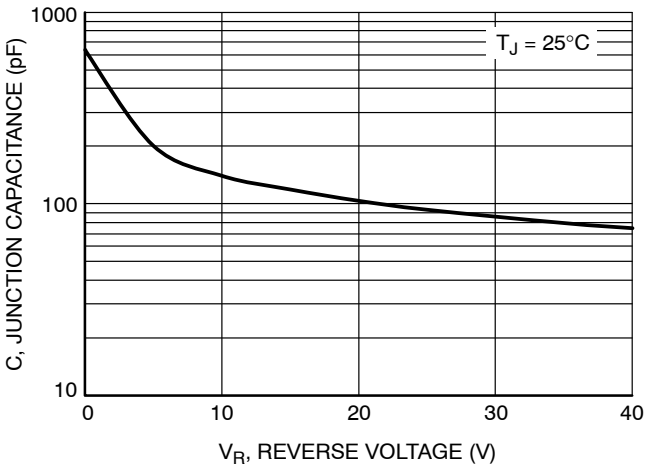


Figure 5. Typical Junction Capacitance

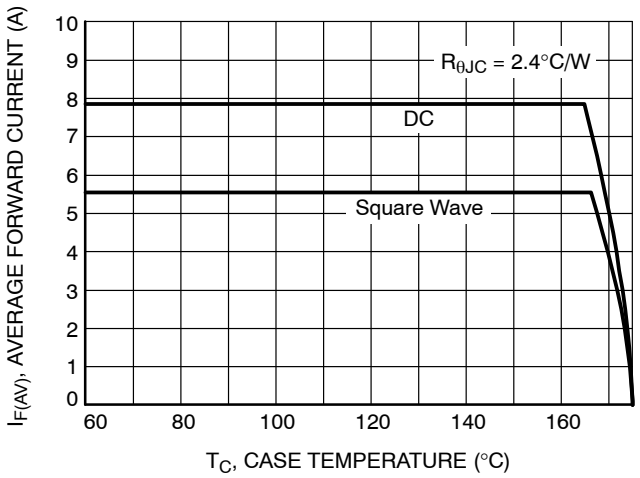


Figure 6. Current Derating TO−220AB

TYPICAL CHARACTERISTICS

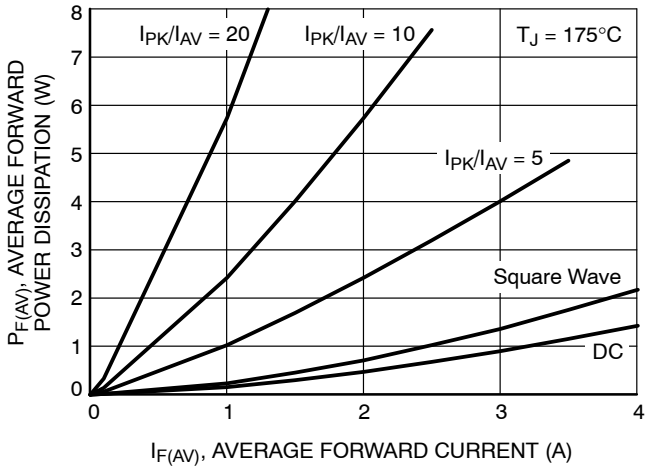


Figure 7. Forward Power Dissipation

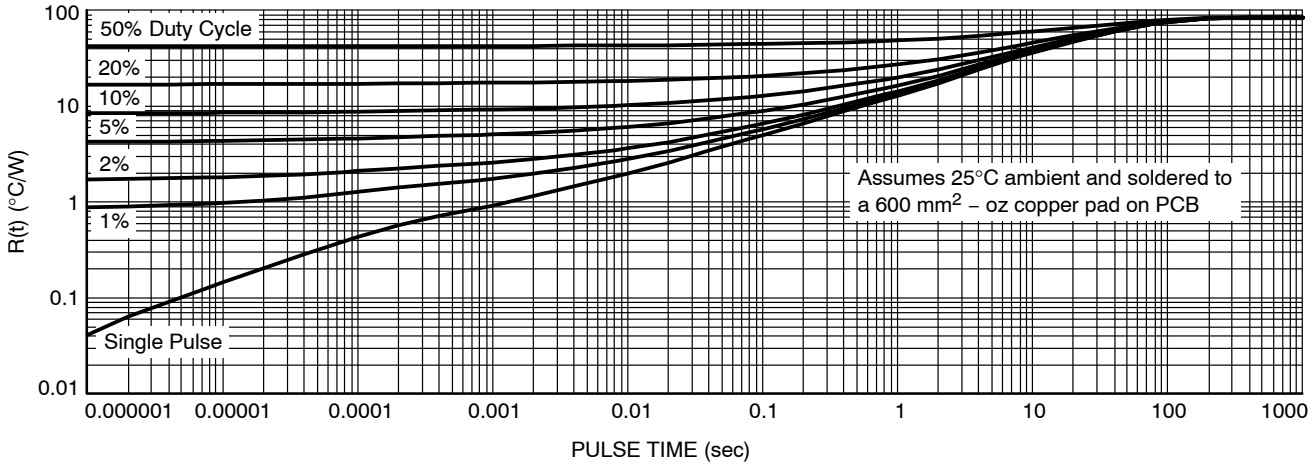
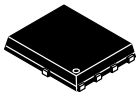


Figure 8. Thermal Characteristics

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

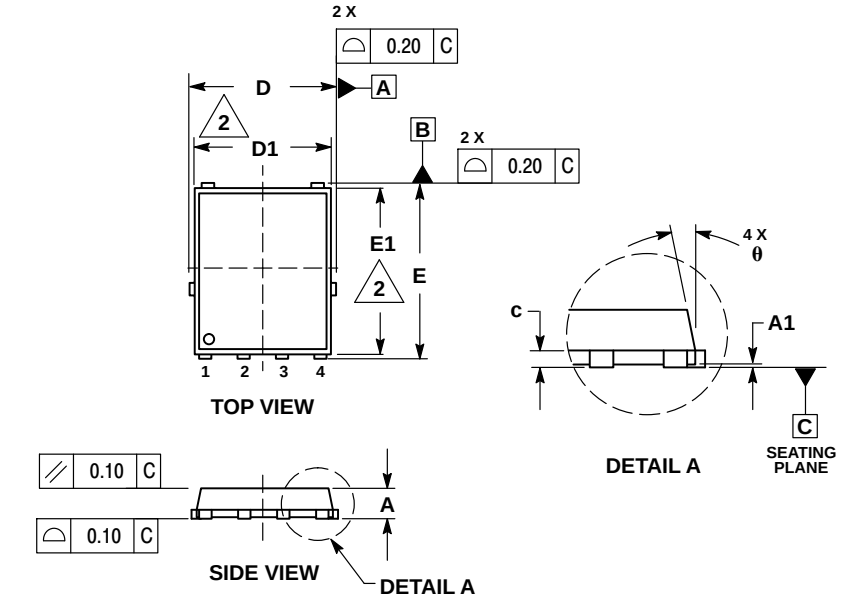
ON Semiconductor®



SCALE 2:1

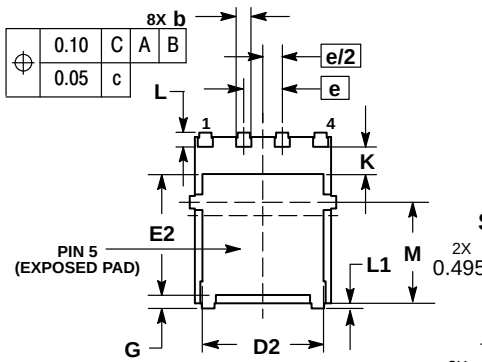
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

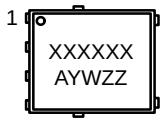


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



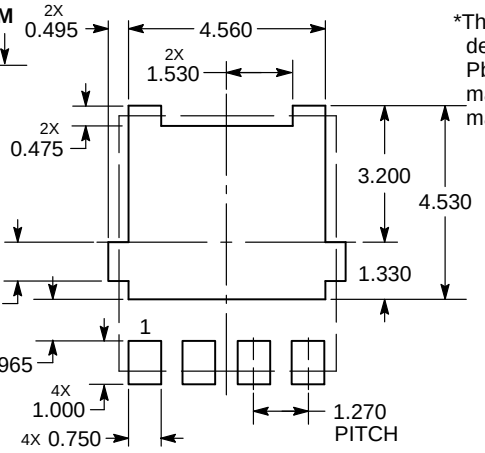
GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

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